Sources of n-type conductivity in $GaInO_3$

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Using hybrid density functional theory, we investigated formation energies and transition energies of possible donor-like defects in $GaInO_3$, with the aim of exploring the sources of the experimentally observed n-type conductivity in this material. We predicted that O vacancies are deep donors; interstitial Ga and In are shallow donors but with rather high formation energies (>2.5 eV). Thus these intrinsic defects cannot cause high levels of n-type conductivity. However, ubiquitous H impurities existing in samples can act as shallow donors. As for extrinsic dopants, substitutional Sn and Ge are shown to act as effective donor dopants and can give rise to highly n-type conductive $GaInO_3$; while substitutional N behaviors as a compensating center. Our results provide a consistent explanation of experimental observations.

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I. INTRODUCTION

Transparent conducting oxides (TCOs) are unique materials which combine concomitant electrical conductivity and optical transparency in a single material. Thus they currently play an important role in a wide range of optoelectronic devices, such as solar cells, flat panel displays and light emitting diodes.[1–8] The ideal TCOs should have a carrier concentration on the order of 10^{20} cm^{-3} and a band-gap energy above 3.1 eV to ensure transparency to visible light. Recently, multicomponent oxide semiconductors have been attracting much attention as new TCOs.[8–11] Monoclinic $GaInO_3$ is a promising TCO due to its excellent optical transmission characteristics.[12–15] It shows a very low optical absorption coefficient on the order of a few hundreds cm^{-1} which is significantly lower those of ITO, ZnO:Al and SnO_2:F in the visible region. It has a refractive index of around 1.65 which matches well with that of glass (∼1.5). Its experimental band-gap is about 3.4 eV. Additionally, it can be well coated on transparent substrate such as glass, fused silica, plastic, and semiconductors. Even in polycrystalline sample, the resistivity is comparable to conventional wide-band-gap transparent conductors such as indium tin oxide, while exhibiting superior light transmission. Particularly in the blue wave length region of the visible spectrum, it exhibits superior light transmission.

The high quality n-type $GaInO_3$ samples with conductivities of over 300 $(\Omega\cdot cm)^{-1}$ through doping Ge and/or Sn have been experimentally synthesized by Phillips and Minami *et al.* respectively.[13,14] They also observed that the carrier concentrations vary strongly with oxygen partial pressure $p(O_2)$ and concluded that oxygen vacancy (V_O) might play a key role as a native donor-like defect present in n-type $GaInO_3$. However, it is generally accepted that V_O cannot produce free electrons due to their deep donor levels even in high concentrations of V_O in many TCOs, such as in ZnO,[16–18] SnO_2[19], In_2O_3[20]. In contrast, ubiquitous H impurities might be responsible for the unintentional n-type conductivity in these materials.[22–26] The structural, bonding, electronic and optical properties of $GaInO_3$ have been investigated in our previous *ab-initio* studies.[21] Despite extremely high n-type conductivity in $GaInO_3$, to date, the origin mechanism of electron carriers is still unclear. Hence, an atomistic detailed understanding on the donor-like intrinsic and extrinsic defects possibly forming in $GaInO_3$ is necessary.

In the present work, we investigated formation energies and transition levels of intrinsic and extrinsic defects which might be responsible for the n-type conductivity based on the hybrid density functional theory.[27–29] The recent development of hybrid density functional theory can yield the experimental band gap values,[30–32] and thus provides more reliable description on formation energies and transition levels of defects in semiconductors.[17–20] We demonstrated that (i) O vacancy and interstitial In as well as interstitial Ga are not responsible for the experimentally observed n-type conductivity of $GaInO_3$; (ii) incorporation of H, Sn and Ge impurities act as shallow donors, which can provide a consistent explanation of experimental observations. (iii) substitutional N on O site acts as a compensating center in n-type $GaInO_3$. The remainder of this paper is organized as follows. In Sec. II, the details of methodology and computational details are described. Sec. III presents our calculated formation energies and transition energies of various donor-like defects in $GaInO_3$. Finally, a short summary is given in Sec. IV.

II. METHODOLOGY

Our total energy and electronic structure calculations were carried out within a revised Heyd-Scuseria-Ernzerhof (HSE06) range-separated hybrid functional[29,33] as implemented in VASP code.[34,35] In the HSE06 approach, the screening parameter μ=0.2 Å^{-1} and the Hartree-Fock (HF) mixing parameter α=28% which means 28% HF exchange with 72% GGA of Perdew, Burke and Ernzerhof (PBE)[36] exchange were chosen to well reproduce the experimental band gap (∼3.4 eV) of $GaInO_3$. The core-valence interaction was described by the frozen-core projector augmented wave (PAW) method.[37,38] The electronic wave functions were expanded in a plane wave basis with a cutoff of 400 eV. The semicore d electrons of both Ga and In atoms were treated as core electrons. Test calculations show that the calculated formation energies of defects differ by less 0.1 eV/atom than those of the corresponding configurations in which the d electrons were included as valence electrons.

As seen in Fig. 1 (a), the monoclinic $GaInO_3$ which has a c2/m space group is characterized by four lattice parameters: three vectors (a, b and c) and the angle β between a and c lattices.[12,13,39] Our previous studies predicted that a, b, c and β are 12.96 Å, 3.20 Å, 6.01 Å and 77.89 ° respectively, with a calculated formation energy of -8.43 eV per formula unit.[21] The local structure of $GaInO_3$ is shown in Fig. 1 (b), one can find that all Ga (In) atoms site tetrahedrally (octahedrally) coordinated. There are three nonequivalent O atoms and we denote them as O(i), O(ii) and O(iii) respectively. The O(i) is threefold coordinated surrounded by two In and one Ga atoms; the O(ii) is also threefold coordinated surrounded by one In and two Ga atoms; while the O(iii) is fourfold coordinated surrounded by three In and one Ga atoms. A more detailed discussions regarding the structural and electronic properties of $GaInO_3$ were given in our previous work.[21]

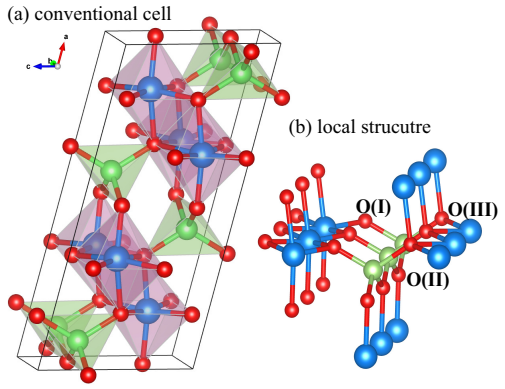

FIG. 1. (Color online) (a) Schematic polyhedral representation of $GaInO_3$ conventional cell; (b) local structure of three nonequivalent O atoms. Green, blue and red balls represent Ga, In and O atoms respectively.

The defective systems were modeled by adding (removing) an atom to (from) a 1×4×2 supercell consisting of 160 atoms. A 2×2×2 k-point mesh within Monkhorst-Pack scheme[40] was applied to the Brillouin-zone integrations in total-energy calculations. The internal coordinates in the defective supercells were relaxed to reduce the residual force on each atom to less than 0.02 eV·Å^{-1}. All defect calculations were spin-polarized. To investigate the source of n-conductivity in $GaInO_3$, the intrinsic donor-like defects, including oxygen vacancy (V_O), interstitial Ga (Ga_i) and In (In_i) were considered in the present work. As for extrinsic impurities, previous experimental findings have shown that substitutional Sn on In sites (Sn_{In}) and Ge on Ga sites (Ge_{Ga}) are effective n-type dopants.[13] Additionally, the incorporation of H and N impurities were also explored since they might act as ubiquitous or purposeful impurities during the growth of $GaInO_3$. There are several possible interstitial sites due to the low symmetry of monoclinic structure. Here we adopted the most favorable interstitial configuration in the β-Ga_2O_3 as discussed in the previous works.[41,42]

In the charged-defect calculations, a uniform background charge was added to keep the global charge neutrality of supercell. The formation energy of a charged defect is defined as:[43]

$$\Delta E_D^f(\alpha,q) = E_{tot}(\alpha,q) - E_{tot}(host,0) - \sum n_\alpha(\mu_\alpha^0+\mu_\alpha) + q(\mu_e+\epsilon_v) + E_{corr}[q], \quad (1)$$

where $E_{tot}(\alpha,q)$ and $E_{tot}(host,0)$ are the total energies of the supercells with and without defect. n_α is the number of atoms of species α added to (n_α>0) or removed from (n_α<0) the perfect supercell to create defect. μ_α^0 is the atomic chemical potential of species α which is equal to the total energy of per atom in its most stable elemental phase, namely, α-Ga, tetragonal-In, α-Sn, Ge, O_2, H_2 and N_2. μ_α is relative chemical potential referenced to the corresponding μ_α^0. q is the charge state of defect and μ_e is electron chemical potential in reference to the host valence band maximum (VBM). Therefore, μ_e can vary between zero and the host band-gap E_g. The final term accounts for both the alignment of the electrostatic potential between the bulk and defective charged supercells, as well as the finite-size effects resulting from the long-range Coulomb interaction of charged defects in a homogeneous neutralizing background, as outlined by Freysoldt *et al.*[44], using a calculated dielectric constant of 10.2.[21] The chemical potential μ_α can vary from O-rich to O-poor limits depending on the growth conditions. The chemical potentials of Ga, In and O atoms are subject to their lower bounds satisfied by the constraint $\mu_{Ga}+\mu_{In}+3\mu_O=\Delta H_f(GaInO_3)$, where $\Delta H_f(GaInO_3)$ is the formation energy of $GaInO_3$. They are subject to the upper bounds $\mu_O\leq 0$ (O-rich limit), $\mu_{Ga}\leq 0$ as well as $\mu_{In}\leq 0$ (O-poor limit). In addition, we examined In_2O_3 and Ga_2O_3 as limiting phases and found that they do not affect our conclusions.

For an extrinsic impurity A (A=Ga, Sn, N and N), $\mu_{\rm A}$ is limited by the formation of its corresponding solid (gaseous) elemental phase. Additionally, $\mu_{\rm A}$ and $\mu_{\rm O}$ are further limited by the formation of secondary phases A_mO_n, namely,

$$\mu_A \leq 0, \tag{2}$$

$$\mu_{\rm In} + \mu_{\rm Ga} + 3\mu_{\rm O} = \Delta H_f({\rm GaInO_3}), \tag{3}$$

$$m\mu_{\rm A} + n\mu_{\rm O} \leq \Delta H_f(A_mO_n). \tag{4}$$

We take substitutional Sn on In site as an example. To avoid the formation of secondary phase SnO_2, $\mu_{\rm Sn}+2\mu_{\rm O} \leq \Delta H_f({\rm SnO_2})$. The O-poor limit (supposing that both In and Sn are rich) is characterized by $\mu_{\rm In}$=0, $\mu_{\rm O}=\frac{1}{3}\Delta H_f({\rm GaInO_3})$, and $\mu_{\rm Sn}<\Delta H_f({\rm SnO_2})$-$\frac{2}{3}\Delta H_f({\rm GaInO_3})$ as well as $\mu_{\rm Sn}$<0 (to avoid the segregation of α-Sn); while the O-rich limit is characterized by $\mu_{\rm O}$=0, $\mu_{\rm In}=\Delta H_f({\rm GaInO_3})$, and $\mu_{\rm Sn}<\Delta H_f({\rm SnO_2})$ as well as $\mu_{\rm Sn}$<0. It is worth mentioning that the HSE06 calculated formation energies of these complexes depend on the HF mixing parameter α. Our calculations show that HSE06 (α=28%) gives a value of -7.30 eV for $\Delta H_f({\rm In_2O_3})$; while HSE06 ($\alpha$=32%) predicts a value of -9.53 eV,[45] which is quite consistent with the experimental data of -9.60 eV.[46] Thus, the available experimental formation energies of A_mO_n, together with HSE06 (α=28%) calculated μ^0_α were adopted to determine the stability of various defects. In other words, the absolute value of the chemical potential μ^{abs}_α is equal to the HSE06 calculated μ_α plus the μ^0_α determined from the experimental formation energies of A_mO_n.

The defect transition (ionization) energy level $\epsilon_\alpha(q/q')$ is defined as the Fermi-level ($E_{\rm F}$) position for which the formation energies of these charge states are equal for the same defect,

$$\epsilon_\alpha(q/q') = [\Delta E^f_D(\alpha, q) - \Delta E^f_D(\alpha, q')]/(q' - q). \tag{5}$$

Specifically, the defect is stable in the charge state q when the $E_{\rm F}$ is below $\epsilon_\alpha(q/q')$, while the defect is stable in the charge state q′ for the $E_{\rm F}$ positions above $\epsilon_\alpha(q/q')$.

III. RESULTS AND DISCUSSION

In semiconductors and insulators, the defect-levels induced by impurities or defects are either located in the band gaps, or resonant inside the continuous host bands. Similar to what was done in our previous studies,[47,48] a semiquantitative model which describes the single particle defect levels for all the considered neutral defects is proposed and displayed in Fig. 2, with the aim of determining the possible charge states and sketchily catching the conductive characteristic of various defects in $GaInO_3$. One can find that $V_{\rm O}$ introduces one doubly-occupied level locating around the host middle gap. Thus its possible charge states could vary from 0 to 2+, implying that $V_{\rm O}$ is a donor-like defect. It is worth mentioning that the positions of defect levels would be changed over the charge state for a given defect. The local magnetic moments of $V^0_{\rm O}$, $V^{1+}_{\rm O}$ and $V^{2+}_{\rm O}$ are predicted to be 0 μ_B, 1 μ_B and 0 μ_B respectively, based on the filling of electrons on this defect level. This is in good agreement with the calculated findings. Considering that the resulting defect level of $V_{\rm O}$ lies deep inside the band gap, $V_{\rm O}$ is expected to be a deep defect and the wave functions of defect states are predicted to be localized around $V_{\rm O}$ and/or its neighbors, showing an atomic-like characteristic. These speculations will be confirmed later by investigating the charge-density distribution together with transition energy levels of $V_{\rm O}$.

The neutral Ga_i creates two singly-occupied levels in the spin-up component, one singly-occupied and one singly-unoccupied levels in the spin-down component. Thus, its possible charge states could range from 1- to 3+. However, it is expected that the formation of Ga^{1-}_i (acting as an acceptor) is energetically unfavored as the electron affinity of Ga ion is relatively low. A similar behavior is found for In_i due to the same valence electron configuration with Ga_i. From Fig. 2 we see that the neutral $Ge_{\rm Ga}$, $Sn_{\rm In}$, $H_{\rm O}$ and H_i introduce one singly-occupied defect level above the host conduction band minimum (CBM) independently. Since the host CBM is lower in energy than these defect levels, the electrons introduced by these impurities will drop to the CBM and occupy the perturbed conduction states. In this case, a delocalized state showing a host-band-like character is created. The system consisting of one of the above-mentioned defects has an odd number of total electrons and carries a total magnetic moments of 1 μ_B.

An occupied level resonant inside the bottom of the host conduction band is the signature of a shallow donor that exhibits hydrogenic effective-mass like characteristics.[49] This delocalized electron at the CBM is loosely bound to the donor whose *core* is now in the charge state of 1+. We expect that $Ge^{1+}_{\rm Ga}$, $Sn^{1+}_{\rm In}$, $H^{1+}_{\rm O}$ and H^{1+}_i are energetically favorable when the electron chemical potential μ_e is below the CBM. In other words, these defect will act as donors and be stable in the 1+ charge state for all positions of the Fermi energy $E_{\rm F}$ in the band gap. The neutral $N_{\rm O}$ is observed to create three singly-occupied levels above the VBM and one singly-unoccupied level just below the CBM. The neutral N_i induces two singly-occupied levels in the spin-up channel above the VBM. Interestingly, both $N_{\rm O}$ and N_i introduce several localized states in the host forbidden bands far below the VBM (not shown in Fig. 2). These defects states will not be further discussed as they do not contribute to the conductivity of $GaInO_3$.

The calculated formation energies of $V_{\rm O}$, Ga_i and In_i as a function of electron chemical potential μ_e are displayed in Fig. 3. For a given value of μ_e, only the energetically stable charge state (with the lowest formation energy) of a specified defect is presented. The Fermi

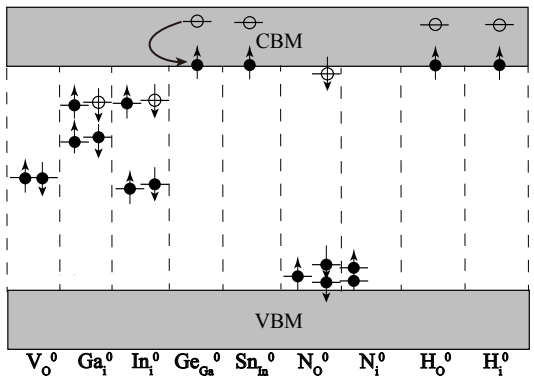

FIG. 2. Semiquantitative single particle defect levels for the neutral intrinsic and extrinsic defects in $GaInO_3$. The filled dots (•) and open dots (○) indicate electrons and holes. The ↑ and ↓ represents spin-up and spin-down components respectively.

energies at which the slopes change correspond to the positions of thermodynamic transition levels. One can note that the calculated transition levels $\epsilon(2+/0)$ of V_O are located between 1.2 and 1.6 eV below CBM depending on the site of V_O. This implies that V_O acts as a deep donor. The V_O^{1+} defects are observed to be not stable for any E_F position. The reason is attributed to the negative-U behavior which lies in the large difference in lattice relaxations between different charge states of V_O. Taken as a whole, one can find that the formation energies and transition energies of oxygen vacancies on three nonequivalent O sites are lightly different due to their distinct local surroundings. The oxygen vacancy on the O(iii) site, henceforth labelled as $V_{O(iii)}$, is the most favorable configuration with a little deeper level of 1.6 eV below CBM. The behaviors of the remaining $V_{O(i)}$ and $V_{O(ii)}$ are almost indistinguishable. Our results on oxygen vacancies are similar to those obtained for β-Ga_2O_3.[42]

In contrast, both Ga_i and In_i act as shallow donors with $\epsilon(1+/0)$ ionization energies of around 0.1 eV and 0.2 eV above CBM respectively. However, their formation energies are more than 2.5 eV even under n-type conditions, in the most favorable O-poor limit. This suggests that the concentration of Ga_i and In_i should be negligible under equilibrium growth conditions. Based on these calculated results, we conclude that the native donor-like defects could not explain the origin of n-type conductivity in $GaInO_3$. On the other hand, note that oxygen vacancies and cation interstitial defects are energetically stable in the 2+ and 3+ charge states respectively, with the calculated formation energies as low as -3.0 eV when the E_F is close to the VBM under O-poor growth conditions. This means that the concentrations of these native donors are high enough to certainly compensate the p-type conductivity of $GaInO_3$ that one wants to create. The formation of these hole-compensating defects can be suppressed by growing in the O-rich limit. More advanced experimental methods, such as nonequilibrium growth techniques may further minimize self-compensation effects in p-type doping $GaInO_3$.

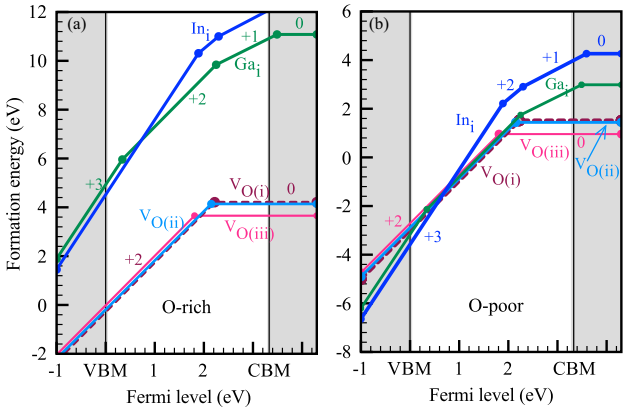

FIG. 3. (Color online) Formation energies of Ga_i, In_i and three nonequivalent O vacancies (V_O) in $GaInO_3$ as a function of Fermi level under (a) extreme oxygen-rich and (b) extreme oxygen-poor conditions. For the V_O, three nonequivalent O vacancies are labeled as $V_{O(i)}$, $V_{O(ii)}$ and $V_{O(iii)}$. The VBM is set to zero.

As for extrinsic impurities, previous experimental findings have shown that Sn and Ge prefer occupying the In and Ga sites respectively.[13] This is attributed to the close ionic radii of Sn (Ge) with In (Ga). The calculated shallowest transition levels are $\epsilon(1+/0)$=3.4 eV for Ge_{Ga} and $\epsilon(1+/0)$=3.5 eV for Sn_{In}, lying just above the CBM. This means that both substitutional Sn on In sites and substitutional Ge on Ga sites are highly effective donor dopants, especially the former with a calculated formation energy of around -1.5 eV under n-type and O-rich conditions. Our findings are in good agreement with experiments which indicate that both In and Ge can significantly enhance the n-conductivity in $GaInO_3$ samples.[13]

The transition energies $\epsilon(0/1-)$ of substitutional N defects on three nonequivalent O sites are higher than 1.5

eV above the VBM. Clearly, N_O is a deep acceptor and will not enable p-type conductivity in $GaInO_3$. A very similar behavior has been reported for the N dopant in ZnO.[50] However, we note that $N_{O(i)}$ is stable in the 1- charge state with a calculated formation energy of around 0.8 eV for the E_F near the host CBM. It is also found that N_O defects have formation energies comparable to, or even lower than those of Ge_{Ga} and Sn_{In} under O-rich conditions but becomes energetically less favorable under O-rich conditions. This suggests that N_O can act as an electron killer and compensate the n-type conductivity of $GaInO_3$. This explains the experimentally observed the decrease trend on the electronic conductivity when the samples were annealed in nitrogen partial pressure. By comparison, N_i is always energetically stable in the neutral state with a rather high formation energy of 6.5 eV, regardless of the position of the E_F. This indicates that N_i is electrically inactive and its concentration should be negligible under equilibrium conditions.

As shown in Fig. 4, all H_O defects in the different configurations act as shallow donors with the (1+/0) thermodynamic transition levels very close to the CBM. Their formation energies are lower under O-poor conditions than under O-rich ones, explaining that the concentration of H_O in the samples increases with the decrease of oxygen partial pressure $p(O_2)$ during growth.[13,14] It is also expected that H impurities will fall into the oxygen vacancy sites, and thus H_O can enhance the electrical conductivity of $GaInO_3$ under oxygen reducing (O-poor) conditions. Besides, H_i is observed to be energetically more stable than H_O, yielding a transition level (+1/0)=3.5 eV, just above the CBM. Hence H_i also behaves exclusively as a shallow donor for any E_F value ranging from the VBM to the CBM. In consideration of the fact that both H_i and H_O serve as shallow donors, the post growth annealing in hydrogen partial pressure could help to reduce the resistivity of n-type $GaInO_3$ samples, as was observed in experiments. Nevertheless, one can find that the positively charged H impurities have formation energies of less than 0.8 eV for the E_F close to VBM, implying that H impurities might act as hole compensating centers in acceptor-doped $GaInO_3$.

To gain a deeper understanding of the defect states from the real space point of view, we take H_O and V_O as examples and plot the wavefunction squared of defect levels induced by them. As we have discussed above, H_O is a typical shallow donor. From the results depicted in Fig. 5 we see that the wave functions of H_O defect states distribute over all O atoms, showing O-2s like and rather delocalized characteristics. The CBM of $GaInO_3$ was observed to be mainly derived from O-2s states.[21] This confirms that the defect level of H_O is resonant inside the bottom of the conduction band as schematized in Fig. 2. As expected, the wave functions of V_O mainly localize at the oxygen vacancy and its seven next nearest-neighbor oxygen atoms, showing a highly-localized characteristic as V_O is a deep donor. A similar behavior has been reported for V_O in ZnO.[18]

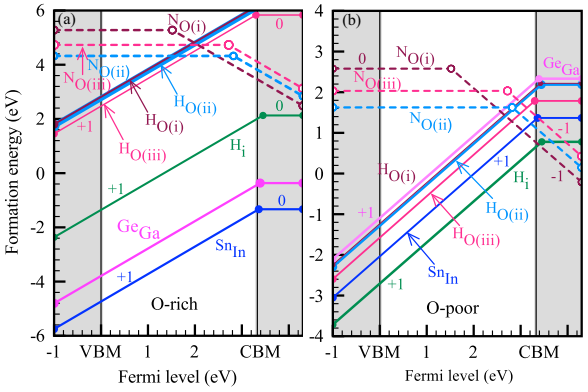

FIG. 4. (Color online) Formation energies of Ge, Sn, H and N impurities in $GaInO_3$ as a function of Fermi level under (a) extreme oxygen-rich and (b) extreme oxygen-poor conditions. The VBM is set to zero.

Considering that the formation energies of charged defects depend on the position of the E_F in the host band gap which is sensitive to the choice of HF mixing parameter α, we take V_O and N_O as examples to investigate the roles of α in their stability and conductivity. From the results reported in Fig. 6 (a), we find that the calculated formation energies of V_O differ less than 0.4 eV for α=15% and 28%. In contrast, the magnitude of band gap significantly decreases from 3.4 eV for α=28% to 2.5 eV for α=15%. The underestimation of band gap using HSE06 (α=15%) method leads to shallower transition levels of ϵ(0/1-)=0.99 eV for N_O and ϵ(2+/0)=1.49 eV for V_O when referred to the corresponding calculated VBM. To have a better understanding of the origins of these observed trends in the transition levels, we plot the transition levels on an absolute energy scale, *e.g.*, referenced to the vacuum level, in Fig. 6 (b). we note that α has almost negligible effects on the transition levels of V_O and N_O defects, with respect to the vacuum level. Nevertheless, the host VBM moves upward, while the CBM moves downward. Consequently, the host band gap de-

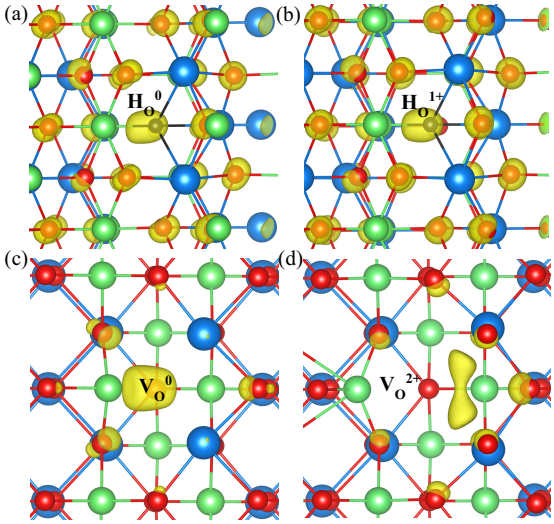

FIG. 5. (Color online) Wavefunction squared for H_O acting as a typical shallow donor in the charge states of (a) 0, (b) 1+. Wavefunction squared for V_O, an example of the typical atomic-like deep donor in the charge states of (c) 0 and (d) 2+. The charge density isosurfaces are shown at 20% of their maximum value. Green, blue, red and black balls represent Ga, In, O and H atoms respectively.

creases along with α. In addition, the magnitude of band offset on valence band is found to be more significantly than that on conduction band. This implies that the transition levels of acceptors should be more sensitive to the choice of α than those of donors in $GaInO_3$. In a word, the transition levels of acceptors and donors become shallow when reducing the value of α from 28% to 15%. The rigid shifts of the host VBM and CBM are primarily responsible for the shallower transition levels which are calculated by using HSE06 (α=15%) approach.

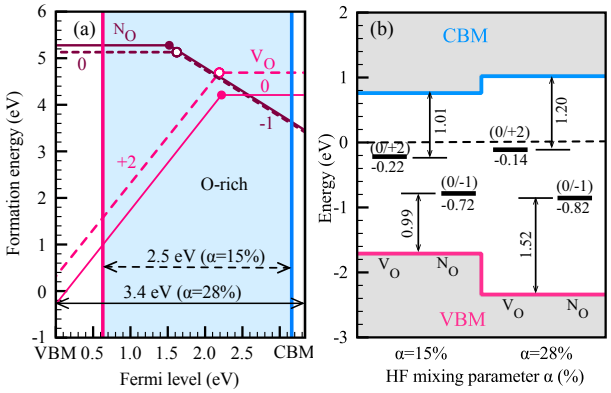

FIG. 6. (Color online) (a) Formation energies of substitutional N and O vacancy as a function of Fermi level under extreme oxygen-rich condition, and (b) transition energy levels referenced to the vacuum level using HSE06 (α=28%) and HSE06 (α=15%) methods respectively. The blue region represents the HSE06 (α=15%) calculated band gap.

IV. SUMMARY

In summary, we performed first-principles calculations based on hybrid density functional theory to systematically explore the behaviors of possible donor-like defects which are ubiquitous or deliberately incorporated into $GaInO_3$ during the synthesis processes. We found that the native defects including O vacancies and interstitial Ga as well as interstitial In cannot contribute to the n-type conductivity of $GaInO_3$ as they are either deep donors or have negligible concentrations. In contrast, our results suggest that Ge, Sn and H impurities act as shallow donors with low formation energies and they are most likely the sources of the n-type conductivity observed in the experiments; while substitutional N acts as a compensating center in n-type $GaInO_3$.

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